# **BUV22**

# **Switch-mode Series NPN Silicon Power Transistor**

This device is designed for high speed, high current, high power applications.

#### **Features**

• High DC Current Gain:

 $h_{FE} \min = 20 \text{ at } I_C = 10 \text{ A}$ 

• Low V<sub>CE(sat)</sub>, V<sub>CE(sat)</sub>

 $max = 1.0 \text{ V at } I_C = 10 \text{ A}$ 

• Very Fast Switching Times:

TF max =  $0.35 \mu s$  at  $I_C = 20 A$ 

• Pb-Free Package is Available\*

#### **MAXIMUM RATINGS**

Rating	Symbol	Value	Unit
Collector–Emitter Voltage	V <sub>CEO(SUS)</sub>	250	Vdc
Collector-Base Voltage	$V_{CBO}$	300	Vdc
Emitter-Base Voltage	V <sub>EBO</sub>	7	Vdc
Collector–Emitter Voltage (V <sub>BE</sub> = -1.5 V)	V <sub>CEX</sub>	300	Vdc
Collector–Emitter Voltage (R <sub>BE</sub> = 100 Ω)	V <sub>CER</sub>	290	Vdc
Collector-Current - Continuous - Peak (PW ≤ 10 ms)	I <sub>C</sub> I <sub>CM</sub>	40 50	Adc Apk
Base-Current Continuous	Ι <sub>Β</sub>	8	Adc
Total Device Dissipation @ T <sub>C</sub> = 25°C	P <sub>D</sub>	250	W
Operating and Storage Junction Temperature Range	T <sub>J</sub> , T <sub>stg</sub>	-65 to 200	°C

#### THERMAL CHARACTERISTICS

Characteristics	Symbol	Max	Unit
Thermal Resistance, Junction-to-Case	$\theta_{JC}$	0.7	°C/W

Maximum ratings are those values beyond which device damage can occur. Maximum ratings applied to the device are individual stress limit values (not normal operating conditions) and are not valid simultaneously. If these limits are exceeded, device functional operation is not implied, damage may occur and reliability may be affected.



### ON Semiconductor®

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# 40 AMPERES NPN SILICON POWER METAL TRANSISTOR 250 VOLTS - 250 WATTS



TO-204AE (TO-3) CASE 197A

#### **MARKING DIAGRAM**



BUV22 = Device Code G = Pb-Free Package A = Assembly Location

Y = Year WW = Work Week MEX = Country of Origin

#### **ORDERING INFORMATION**

Device	Package	Shipping
BUV22	TO-204	100 Units / Tray
BUV22G	TO-204 (Pb-Free)	100 Units / Tray

<sup>\*</sup>For additional information on our Pb–Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

### **BUV22**

## **ELECTRICAL CHARACTERISTICS** ( $T_C = 25^{\circ}C$ unless otherwise noted)

	Characteristic	Symbol	Min	Max	Unit
OFF CHARACTERISTICS (Note	e 1)				
Collector–Emitter Sustaining Vo	-	V <sub>CEO(sus)</sub>	250		Vdc
Collector Cutoff Current at Rev $(V_{CE} = 300 \text{ V}, V_{BE} = -1.5 \text{ V})$ $(V_{CE} = 300 \text{ V}, V_{BE} = -1.5 \text{ V})$		ICEX		3.0 12.0	mAdc
Collector–Emitter Cutoff Currer (V <sub>CE</sub> = 200 V)	nt	I <sub>CEO</sub>		3.0	mAdc
Emitter–Base Reverse Voltage (I <sub>E</sub> = 50 mA)		V <sub>EBO</sub>	7		V
Emitter–Cutoff Current (V <sub>EB</sub> = 5 V)		I <sub>EBO</sub>		1.0	mAdc
SECOND BREAKDOWN		<u> </u>		•	
Second Breakdown Collector C (V <sub>CE</sub> = 20 V, t = 1 s) (V <sub>CE</sub> = 140 V, t = 1 s)	Current with base forward biased	I <sub>S/b</sub>	12 0.15		Adc
ON CHARACTERISTICS (Note	1)			•	•
DC Current Gain (I <sub>C</sub> = 10 A, V <sub>CE</sub> = 4 V) (I <sub>C</sub> = 20 A, V <sub>CE</sub> = 4 V)		h <sub>FE</sub>	20 10	60	
Collector–Emitter Saturation Vo ( $I_C = 10 \text{ A}, I_B = 1 \text{ A}$ ) ( $I_C = 20 \text{ A}, I_B = 2.5 \text{ A}$ )	oltage	V <sub>CE(sat)</sub>		1.0 1.5	Vdc
Base–Emitter Saturation Voltage (I <sub>C</sub> = 40 A, I <sub>B</sub> = 4 A)		V <sub>BE(sat)</sub>		1.5	Vdc
DYNAMIC CHARACTERISTICS	3	,			•
Current Gain — Bandwidth Pro (V <sub>CE</sub> = 15 V, I <sub>C</sub> = 2 A, f = 4 M		f <sub>T</sub>	8.0		MHz
SWITCHING CHARACTERISTI	CS (Resistive Load)	<u>.                                      </u>		•	•
Turn-on Time		t <sub>on</sub>		0.8	μs
Storage Time	$(I_C = 20 \text{ A}, I_{B1} = I_{B2} = 2.5 \text{ A},$ $V_{CC} = 100 \text{ V}, R_C = 5 \Omega)$	t <sub>s</sub>		2.0	1
Fall Time	100 100 1,110 0 22)	t <sub>f</sub>		0.35	<u> </u>
-					

<sup>1.</sup> Pulse Test: Pulse Width  $\leq 300 \,\mu\text{s}$ , Duty Cycle  $\leq 2\%$ .

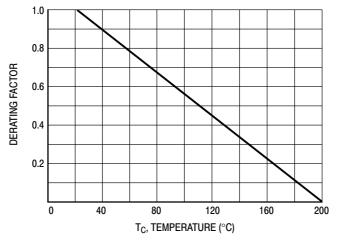


Figure 1. Power Derating

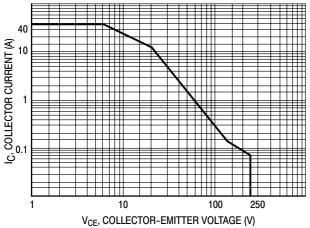


Figure 2. Active Region Safe Operating Area

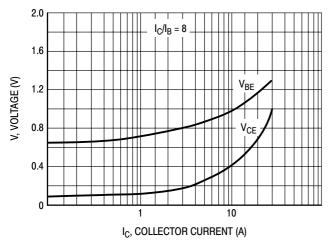


Figure 3. "On" Voltages

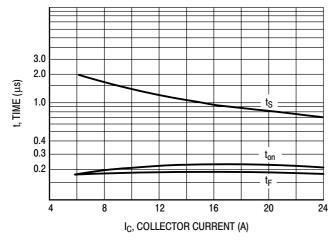


Figure 5. Resistive Switching Performance

There are two limitations on the power handling ability of a transistor: average junction temperature and second breakdown. Safe operating area curves indicate  $I_C - V_{CE}$  limits of the transistor that must be observed for reliable operation i.e., the transistor must not be subjected to greater dissipation than the curves indicate.

The data of Figure 2 is based on  $T_C = 25^{\circ}C$ ;  $T_{J(pk)}$  is variable depending on power level. Second breakdown limitations do not derate the same as thermal limitations.

At high case temperatures, thermal limitations will reduce the power that can handled to values less than the limitations imposed by second breakdown.

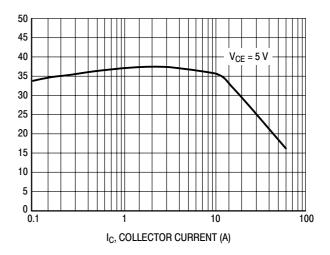
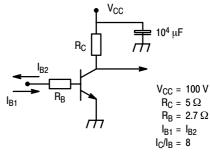


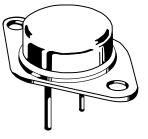
Figure 4. DC Current Gain



R<sub>C</sub> - R<sub>B</sub>: Non inductive resistances

Figure 6. Switching Times Test Circuit

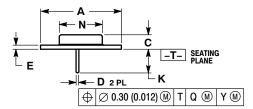


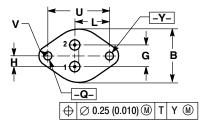


TO-204 (TO-3) **CASE 197A-05 ISSUE K** 

**DATE 21 FEB 2000** 

#### SCALE 1:1





STYLE 1: PIN 1. BASE 2. EMITTER CASE: COLLECTOR

STYLE 2: PIN 1. EMITTER 2. BASE

CASE: COLLECTOR

STYLE 3: PIN 1. GATE 2. SOURCE CASE: DRAIN

STYLE 4: PIN 1. ANODE = 1 2. ANODE = 2 CASE: CATHODES

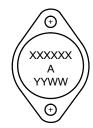
- NOTES:

  1. DIMENSIONING AND TOLERANCING PER
  ANSI Y14.5M, 1982.

  2. CONTROLLING DIMENSION: INCH.

	INC	CHES MILLIMETERS		
DIM	MIN	MAX	MIN	MAX
Α	1.530	REF	38.86 REF	
В	0.990	1.050	25.15	26.67
C	0.250	0.335	6.35	8.51
D	0.057	0.063	1.45	1.60
Е	0.060	0.070	1.53	1.77
G	0.430	BSC	10.92 BSC	
Н	0.215	BSC	5.46 BSC	
K	0.440	0.480	11.18	12.19
L	0.665 BSC		16.89 BSC	
N	0.760	0.830	19.31	21.08
Q	0.151	0.165	3.84	4.19
כ	1.187	1.187 BSC		BSC
٧	0.131	0.188	3.33	4.77

#### **GENERIC MARKING DIAGRAM\***



XXXXX = Specific Device Code = Assembly Locationa Α

YY = Year WW = Work Week

\*This information is generic. Please refer to device data sheet for actual part marking.

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PAGE 2 OF 2

ISSUE	REVISION	DATE
K	LEGALLY CHANGED TO ON	21 FEB 2000

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